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(54) Title: TWO-STAGE PROCESS FOR OBTAINING SIGNIFICANT OLEFIN YIELDS FROM RESIDUA FEEDSTOCKS ✓

(57) Abstract

A two-stage process for obtaining a substantial amount of olefinic product from a residua feedstock. The first stage is comprised of a thermal process unit containing a reaction zone comprised of a horizontal moving bed of fluidized hot particles operated at temperatures from about 500 to 600 °C and having a short vapor residence time, and the second stage thermal conversion zone operated at a temperature of about 700 °C to about 1100 °C, and also having a short vapor residence time.